

	Type	L #	Hits	Search Text	DBs
1	BRS	L3	390	"257"/\$.ccls. and MOSFET with (chip die ic) and wire and (encapsulat\$3 resin epoxy) and lead	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L6	34	"361"/\$.ccls. and MOSFET with (chip die ic) and wire and (encapsulat\$3 resin epoxy) and lead	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L7	143	"438"/\$.ccls. and MOSFET with (chip die ic) and wire and (encapsulat\$3 resin epoxy) and lead	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L8	7	("4032706" "4124864" "4320412" "4546374" "4916518" "5545846" "5592019").PN.	US- PGPUB; USPAT; USOCR
5	BRS	L9	4	("4796078" "5047837" "5172214" "5365106").PN.	US- PGPUB; USPAT; USOCR

	Type	L #	Hits	Search Text	DBs
6	BRS	L10	13	"29"/\$.ccls. and MOSFET with (chip die ic) and wire and (encapsulat\$3 resin epoxy) and lead	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B